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Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet

1

of

2

Complete if Known

Application Number

Not Yet Assigned

Filing Date

February 27, 2004

First Named Inventor

Paul A. Farrar

Group Art Unit

unknown

Examiner Name

unknown

Attorney Docket Number

2269-5570.1US (02-1122.01/US)

U.S. PATENT DOCUMENTS

[illegible]

FOREIGN PATENT DOCUMENTS

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**Examiner
Signature**

Date Considered

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		First Named Inventor	Paul A. Farrar
		Group Art Unit	unknown
		Examiner Name	unknown
		Attorney Docket Number	2269-5570 IUS (02-1122 01/IUS)
Sheet	2	of	2

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials *	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
		ANDRICACOS, Panos C., "Copper On-Chip Interconnections", The Electrochemical Society Interface, Spring 1999, pp. 32-39, Vol. 8, No. 1.	
		BRAUD et al., "Ultra Thin Diffusion Barriers for Cu Interconnections at the Gigabit Generation and Beyond", VMIC Conference, June 1996, pp. 174-179, 1996 ISMIC - 106/96/0174(c).	
		de FELIPE et al., "Electrical Stability and Microstructural Evolution in Thin Films of High Conductivity Copper Alloys", IEEE, 1999, ITC 99/293-295.	
		DING et al., "Copper Barrier, Seed Layer and Planarization Technologies", VMIC Conference, June 1997, pp. 87-92, 1997 ISMIC - 107/97/0087(c).	
		GODBEY et al., "Copper Diffusion in Organic Polymer Resists and Inter-Level Dielectrics", Thin Solid Films, 31 Oct. 1997, pp. 470-474, Vols. 308-309.	
		HUANG et al., "Structure and Electrical Properties of Amorphous W-Si-N Barrier Layer for Cu Interconnections", VMIC Conference, June 1996, pp. 168-173, 1996 ISMIC - 106/96/0168(c).	
		International Conference on Metallurgical Coatings and Thin Films, Program and Abstracts, April 1997, pp. 309, 313.	
		"Improved Metallurgy for Wiring Very Large Scale Integrated Circuits", International Technology Disclosures, 25 Sept. 1986, 1 page, Vol. 4, No. 9.	
		LYMAN et al., "Metallography, Structures and Phase Diagrams", Metals Handbook, 8 th Edition, date unknown, pp. 300-302, Vol. 8, Metals Park, Ohio.	
		MARCADAL et al., "OMCVD Copper Process for Dual Damascene Metallization", VMIC Conference, June 1997, pp. 93-98, 1997 ISMIC - 107/97/0093(c).	
		MURARKA et al., "Copper Interconnection Schemes: Elimination of the Need of Diffusion Barrier/Adhesion Promoter by the Use of Corrosion Resistant, Low Resistivity Doped Copper", SPIE, Jan 1994, ppg. 80-90, Vol. 2335.	
		RYU et al., "Barriers for Copper Interconnections", Solid State Technology, April 1999, pp. 1-6, Vol. 42, Issue 4, p53.	
		SAARIVIRTA, Matti J., "High Conductivity Copper-Rich Cu-Zr Alloys", Transactions of the Metallurgical Society of AIME, June 1960, pp. 431-437, Vol. 218, New York, NY.	

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